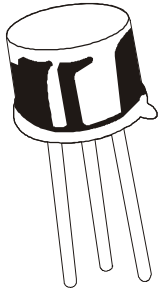


NPN SILICON EPITAXIAL TRANSISTOR

**BFX34
TO-39**



NPN Transistor in a TO-39 Metal Envelope Primarily Intended For Use As High-Current Switching Device, e.g. Inverters And Switching Regulators.

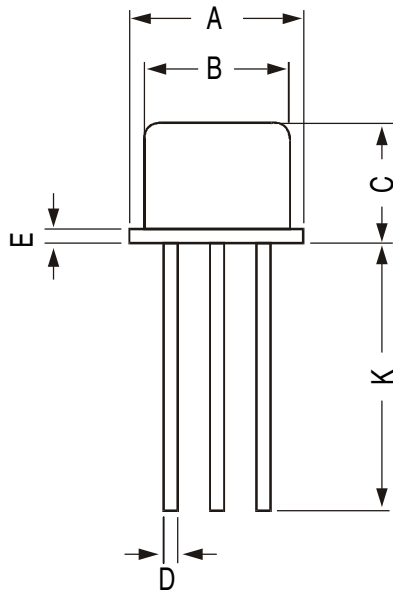
ABSOLUTE MAXIMUM RATINGS

DESCRIPTION	SYMBOL	VALUE	UNIT
Collector -Base Voltage	VCBO	120	V
Collector -Emitter Voltage	VCEO	60	V
Emitter Base Voltage	VEBO	6.0	V
Collector Current (d.c)	IC	2.0	A
Collector Current (peak-value)	ICM	5.0	A
Base Current (d.c)	IB	1.0	A
Power Dissipation up to Tcase=25 deg C	Ptot	5.0	W
up to Tamb=25 deg C	Ptot	0.87	W
Junction and Storage Temperature Range	Tj,Tstg	-55 to +200	deg C
THERMAL RESISTANCE			
Junction to Ambient	Rth (j-a)	200	K/W
Junction to Case	Rth (j-c)	35	K/W

ELECTRICAL CHARACTERISTICS (TA=25 deg C unless otherwise specified)

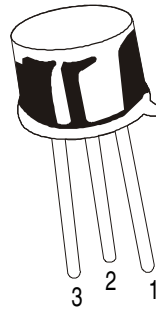
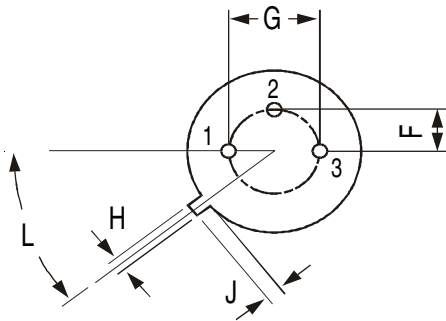
	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Collector Cut off Current	ICES	VCE=60V, VEB=0	-	-	10	uA
Emitter Cut off Current	IEBO	VEB=4V, IC=0	-	-	10	uA
Collector Emitter Saturation Voltage	VCE(Sat)	IC=5A, IB=0.5A	-	-	1.0	V
Base Emitter Saturation Voltage	VBE(Sat)	IC=5A, IB=0.5A	-	-	1.8	V
DC Current Gain	hFE	IC=1A, VCE=2V	-	30	-	
		IC=1.5A, VCE=0.6V	-	60	-	
		IC=2A, VCE=2V	40	-	150	
Collector Capacitance	Cc	VCB=10V, IE=Ie=0 f=1MHz	-	36	-	pF
Emitter Capacitance	Ce	VEB=0.5V, IC=Ic=0 f=1MHz	-	440	-	pF
Transition Frequency	ft	IC=0.5A, VCE=5V f=35MHz	70	-	-	MHz
Turn on Time When Switched From	ton	VBE=2V to IC=5V, IB=0.5A With IBM= 0,5A	-	-	0.60	us
Turn on Time When Switched From	toff	IC=5A, IB=0.5A, to - VBE=2V with -IBM =0.5A	-	-	1.2	us

TO-39 Metal Can Package



DIM	MIN	MAX
A	8.50	9.39
B	7.74	8.50
C	6.09	6.60
D	0.40	0.53
E	—	0.88
F	2.41	2.66
G	4.82	5.33
H	0.71	0.86
J	0.73	1.02
K	12.70	—
L	42 DEG	48 DEG

All dimensions are in mm



PIN CONFIGURATION

1. EMITTER
2. BASE
3. COLLECTOR

Packing Detail

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	Gr Wt
TO-39	500 pcs/polybag	540 gm/500 pcs	3" x 7.5" x 7.5"	20.0K	17" x 15" x 13.5"	32.0K	40 kgs

Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Discrete Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished on the CDIL Web Site/CD is believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Discrete Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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